

FIGURE 6.17 Coupling to floating victim

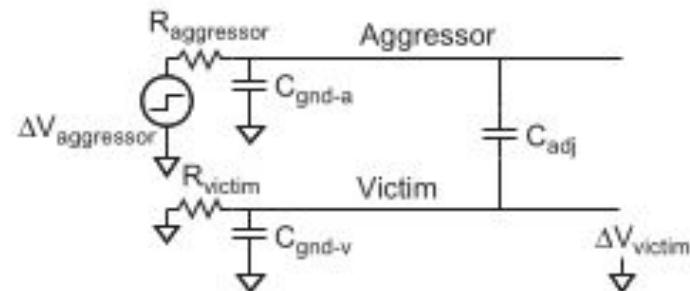


FIGURE 6.18 Coupling to driven victim

$$\Delta V_{\text{victim}} = \frac{C_{\text{adj}}}{C_{\text{gnd-v}} + C_{\text{adj}}} \Delta V_{\text{aggressor}}$$

$$\Delta V_{\text{victim}} = \frac{C_{\text{adj}}}{C_{\text{gnd-v}} + C_{\text{adj}}} \frac{1}{1+k} \Delta V_{\text{aggressor}}$$

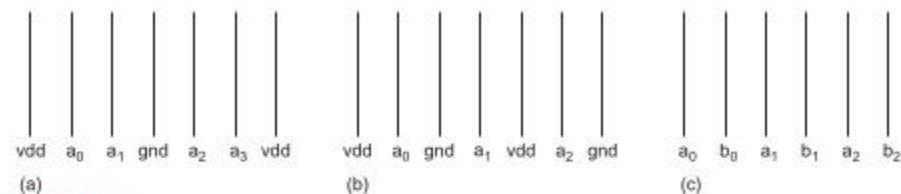


FIGURE 6.28 Wire shielding topologies

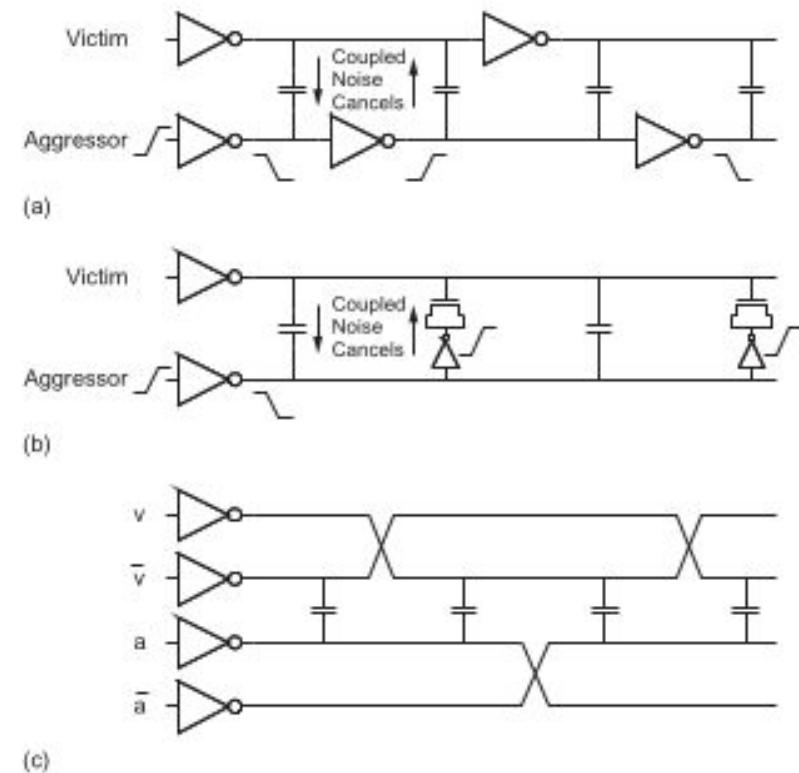
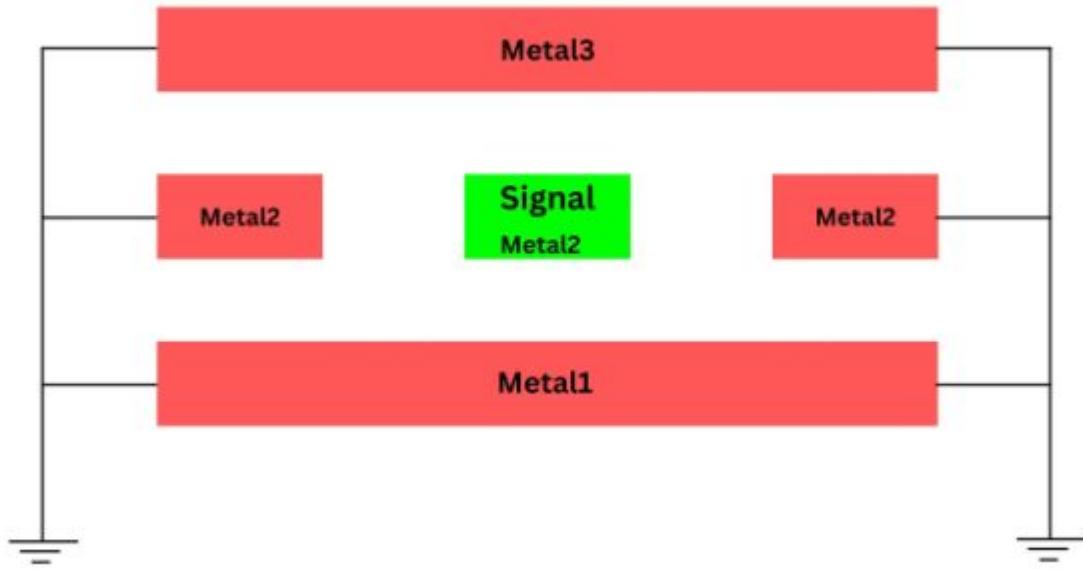
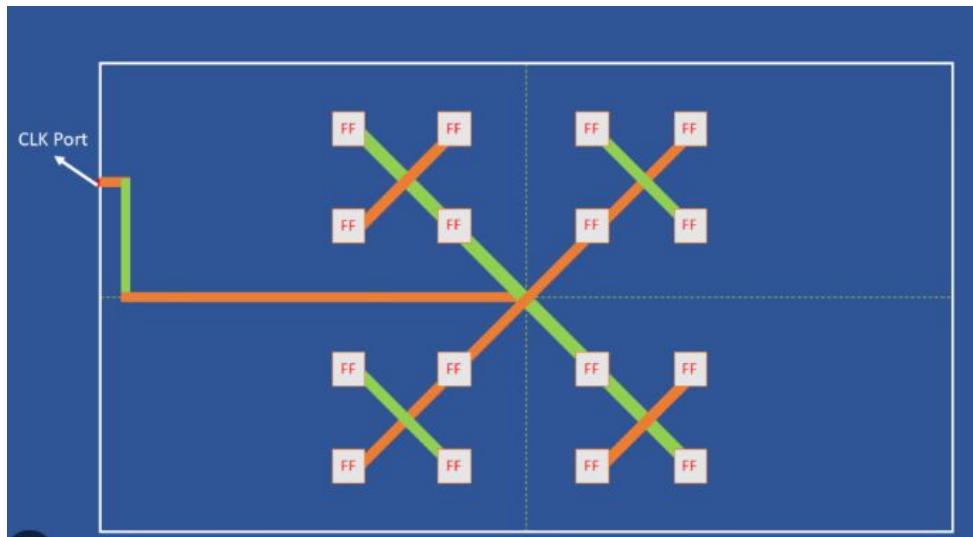
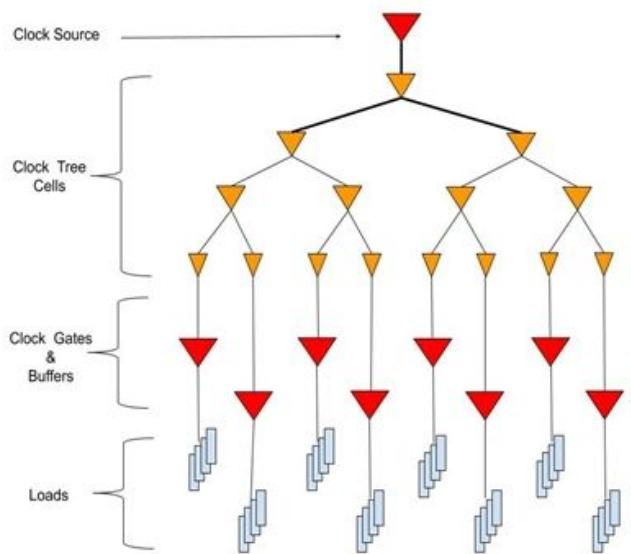
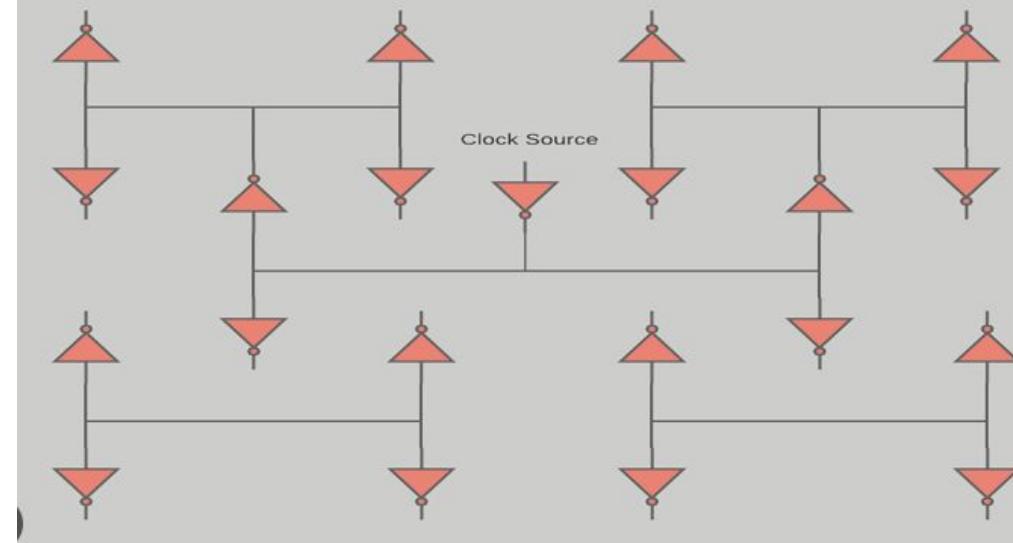
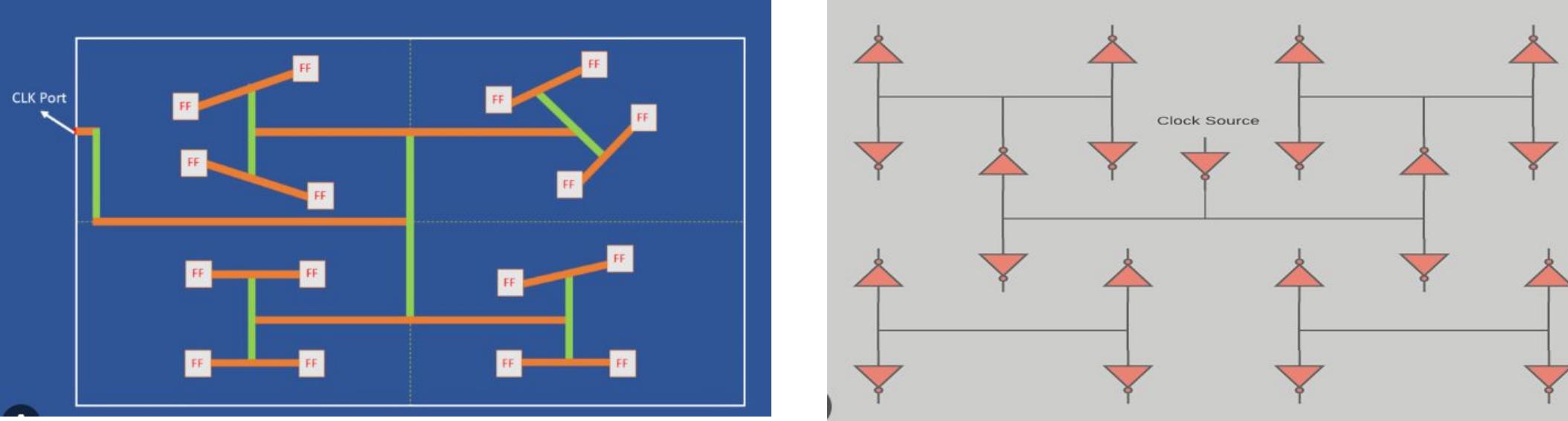


FIGURE 6.29 Crosstalk control schemes



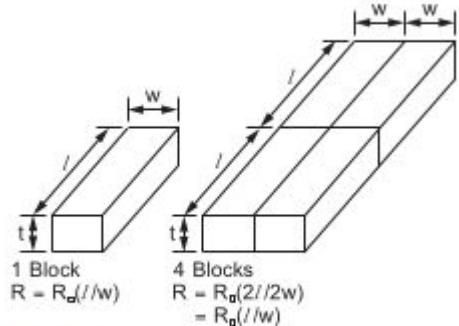


FIGURE 6.6

Two conductors with equal resistance

TABLE 6.2 Bulk resistivity of pure metals at 22 °C

Metal	Resistivity ($\mu\Omega \cdot \text{cm}$)
Silver (Ag)	1.6
Copper (Cu)	1.7
Gold (Au)	2.2
Aluminum (Al)	2.8
Tungsten (W)	5.3
Molybdenum (Mo)	5.3
Titanium (Ti)	43.0

Compute the sheet resistance of a 0.22 μm thick Cu wire in a 65 nm process. Find the total resistance if the wire is 0.125 μm wide and 1 mm long. Ignore the barrier layer and dishing.

SOLUTION: The sheet resistance is

$$R_{\square} = \frac{2.2 \times 10^{-8} \Omega \cdot \text{m}}{0.22 \times 10^{-6} \text{ m}} = 0.10 \Omega/\square \quad (6.4)$$

The total resistance is

$$R = (0.10 \Omega/\square) \frac{1000 \mu\text{m}}{0.125 \mu\text{m}} = 800 \Omega \quad (6.5)$$

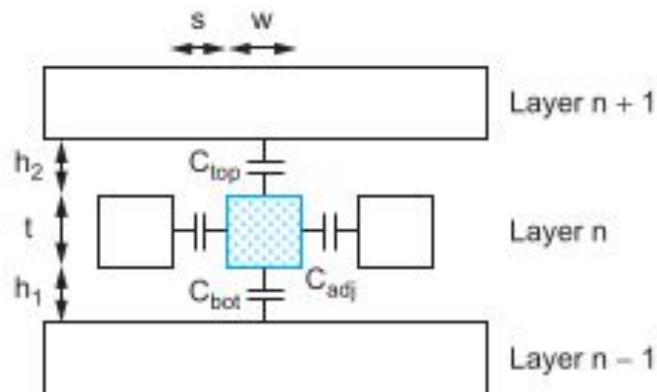


FIGURE 6.11 Multilayer capacitance model

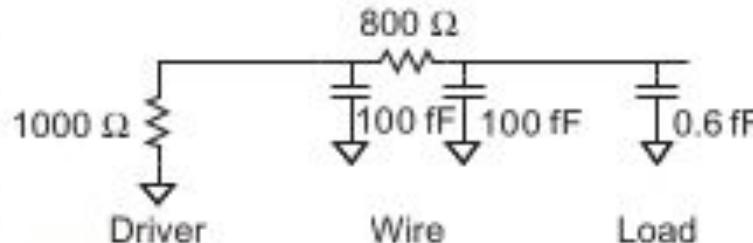


FIGURE 6.14 Equivalent circuit for example

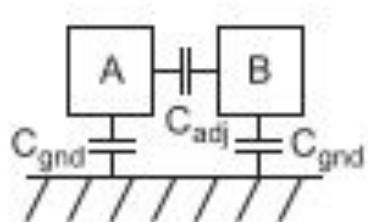
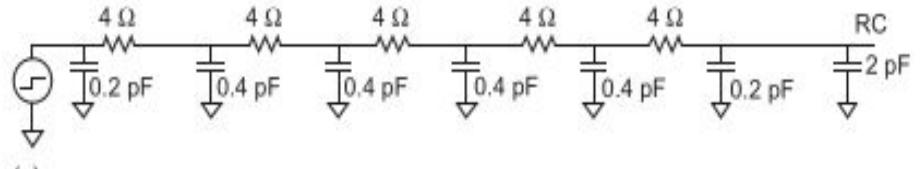
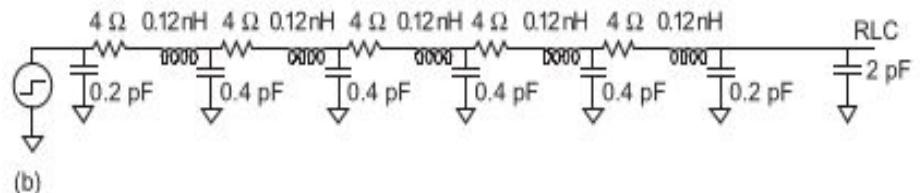


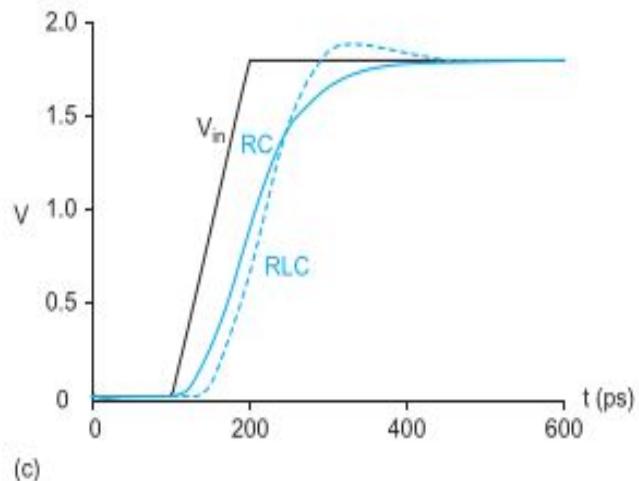
FIGURE 6.16 Capacitances to adjacent neighbor and to ground



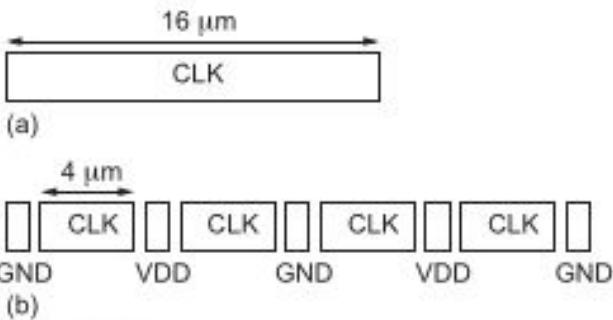
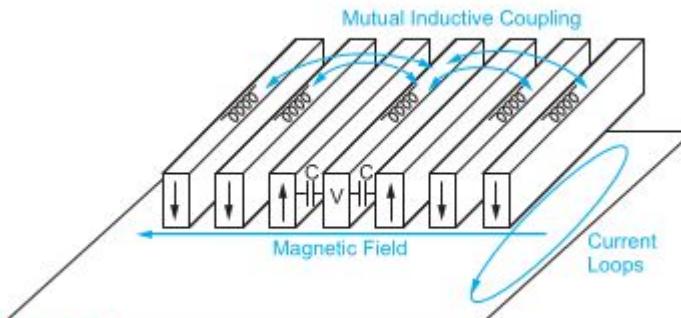
(a)



(b)



(c)

FIGURE 6.21 Wide clock line modeled with and without inductance**FIGURE 6.22** Wide clock line interdigitated with power and ground lines to reduce inductance**FIGURE 6.23** Inductive and capacitive crosstalk in a bus

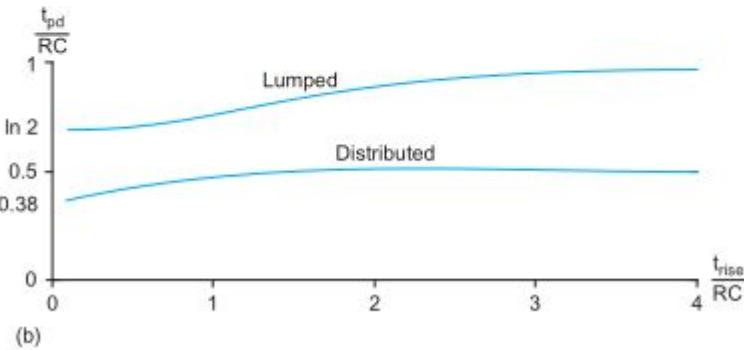
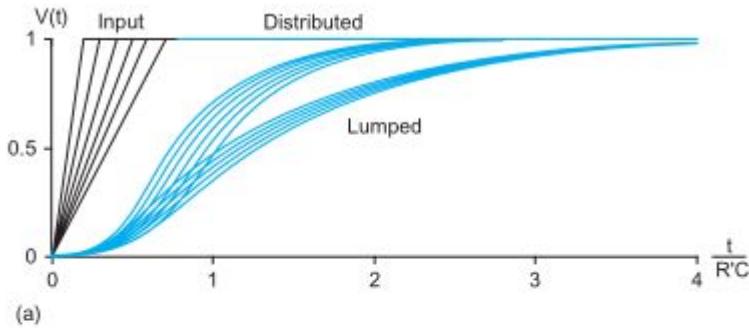


FIGURE 6.25 Effect of rise time on lumped and distributed RC circuit delays

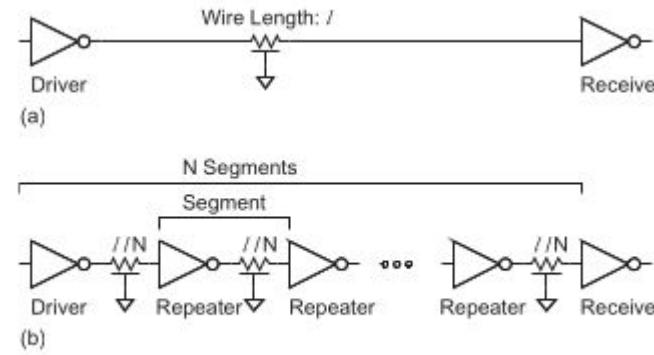


FIGURE 6.26 Wire with and without repeaters

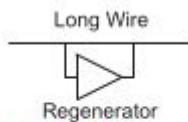


FIGURE 6.31

Regenerator

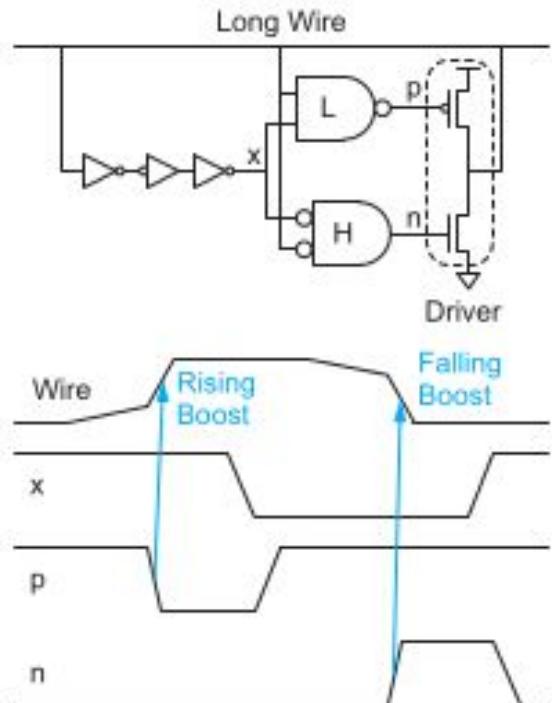
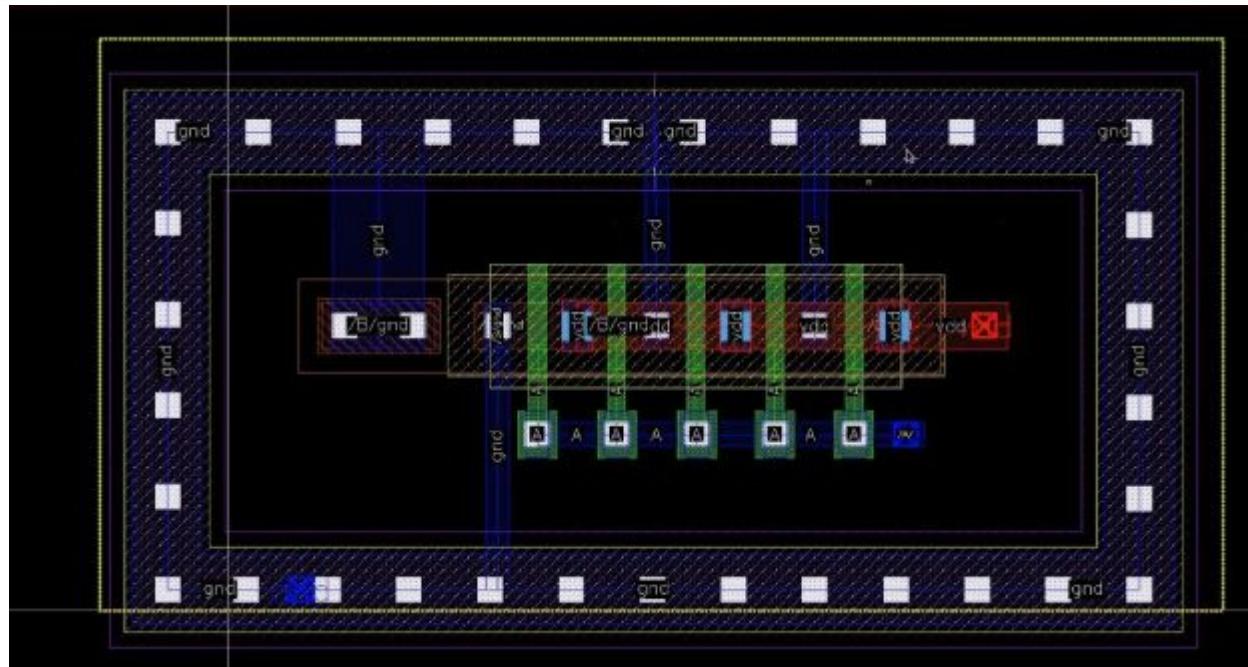
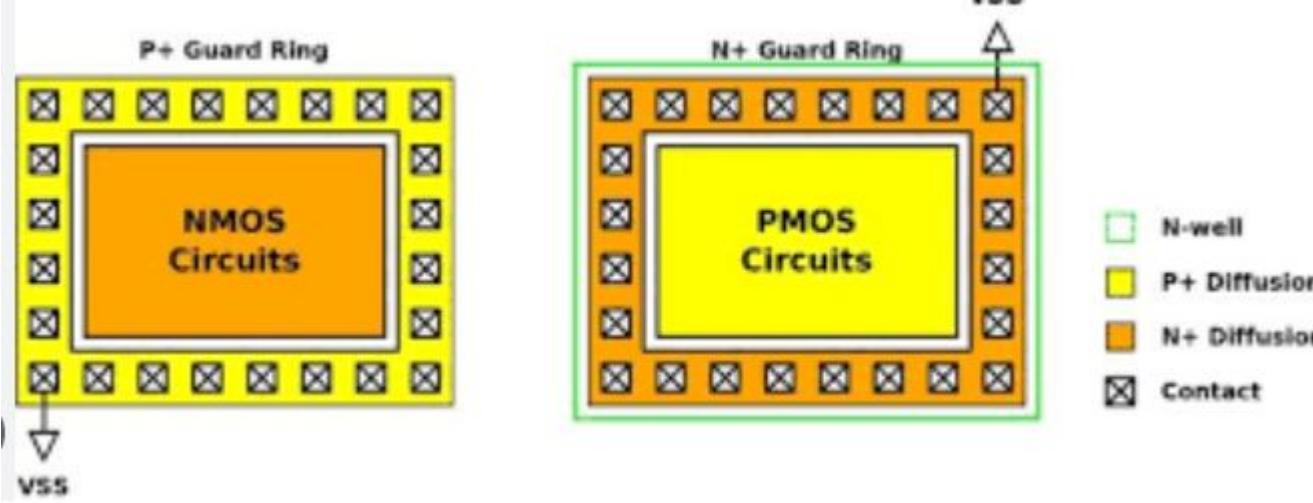
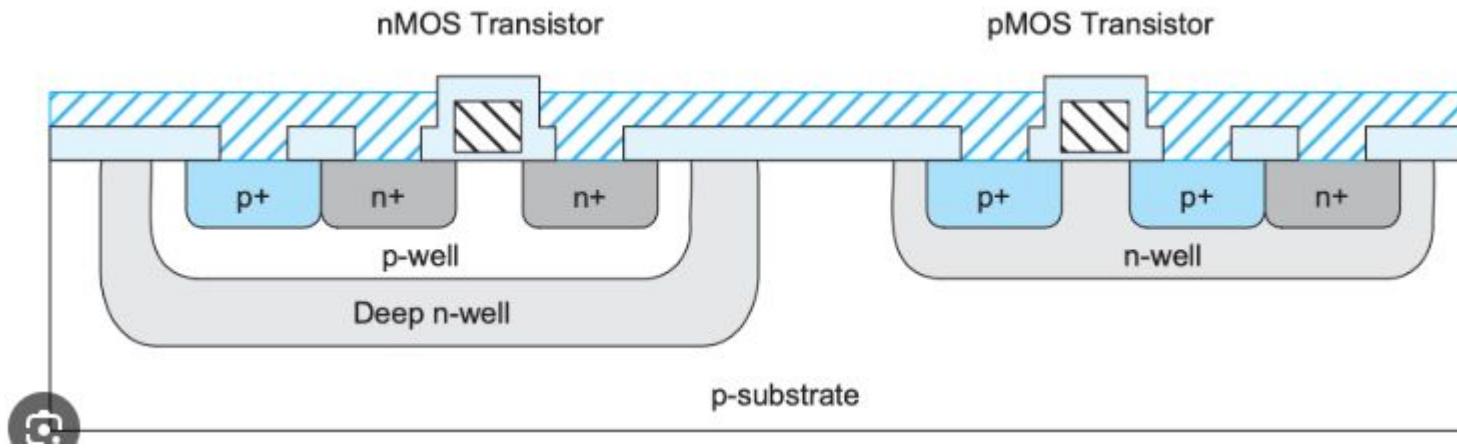
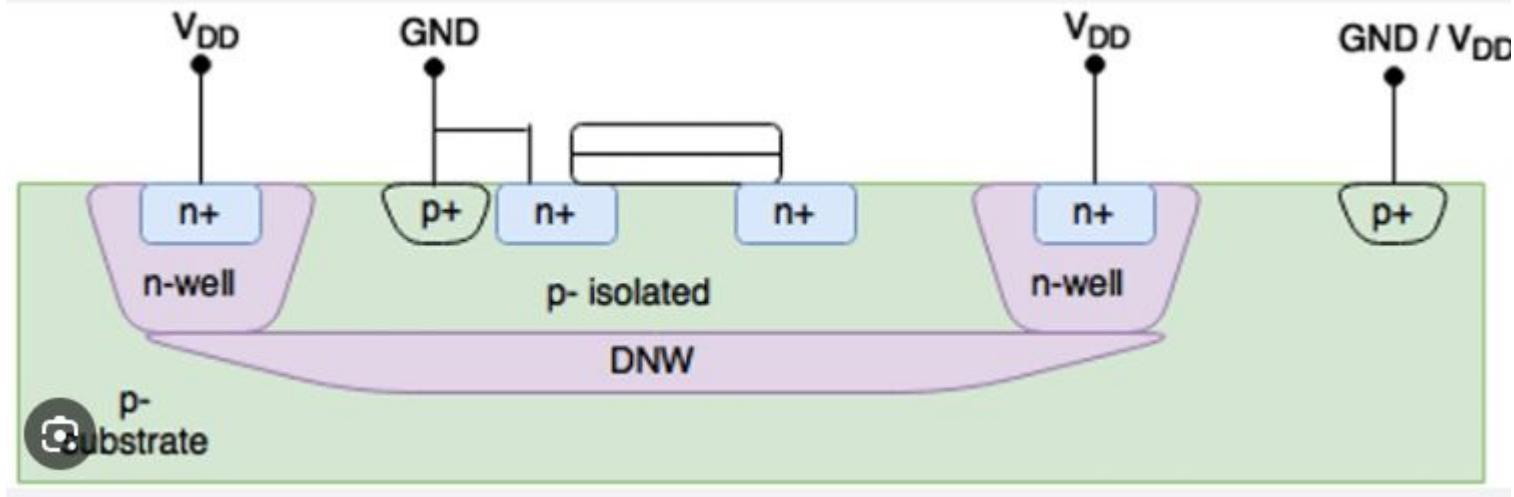
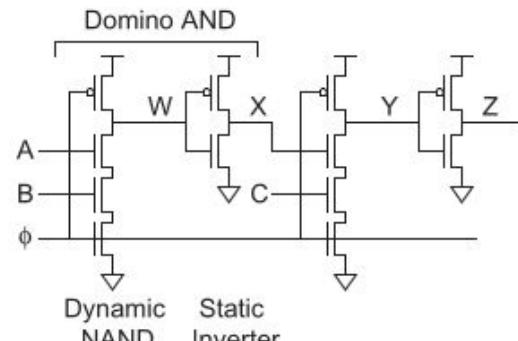


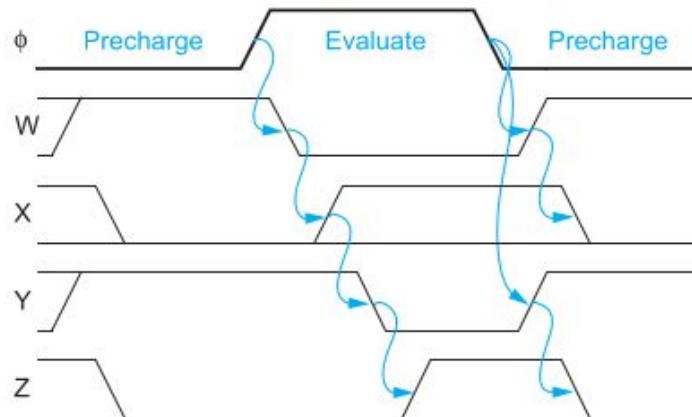
FIGURE 6.32 Regenerator







(a)



(b)

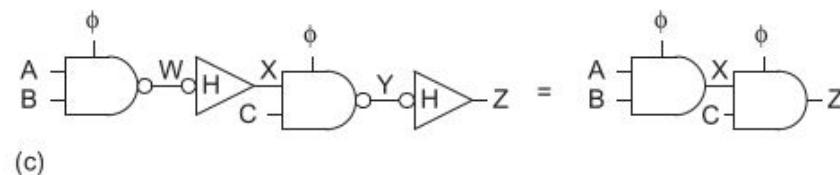
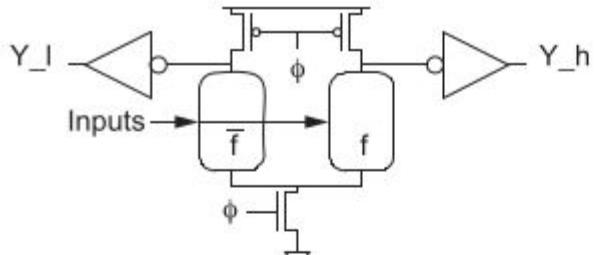
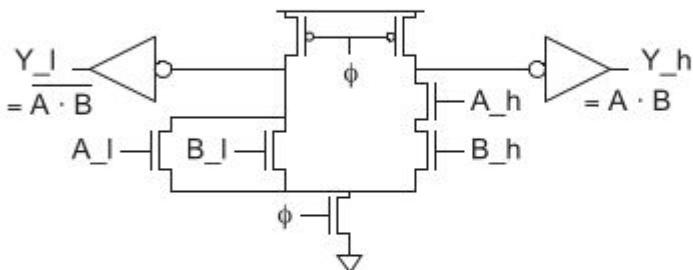


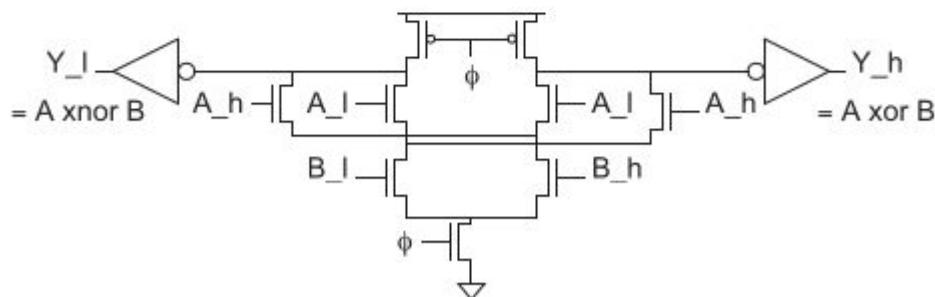
FIGURE 9.28 Domino gates



(a)



(b)



(c)

FIGURE 9.30 Dual-rail domino gates

TABLE 9.2 Dual-rail domino signal encoding

<i>sig_h</i>	<i>sig_l</i>	Meaning
0	0	Precharged
0	1	'0'
1	0	'1'
1	1	Invalid

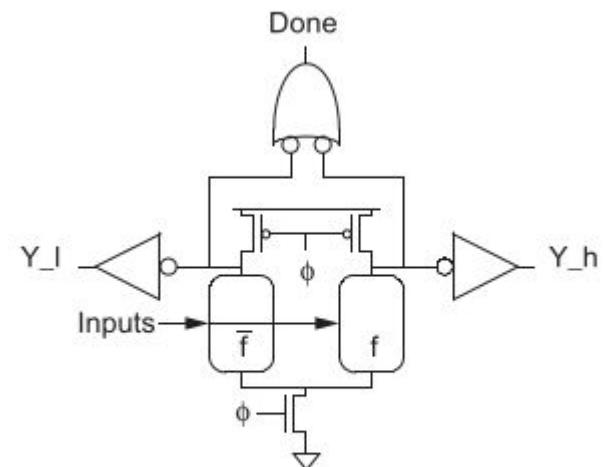


FIGURE 9.31 Dual-rail domino gate with completion detection

Multiple-Output Domino Logic (MODL)

$$c_1 = g_1 + p_1 c_0$$

$$c_2 = g_2 + p_2(g_1 + p_1 c_0)$$

$$c_3 = g_3 + p_3(g_2 + p_2(g_1 + p_1 c_0))$$

$$c_4 = g_4 + p_4(g_3 + p_3(g_2 + p_2(g_1 + p_1 c_0)))$$

$$g_i = a_i b_i$$

$$p_i = a_i \oplus b_i$$

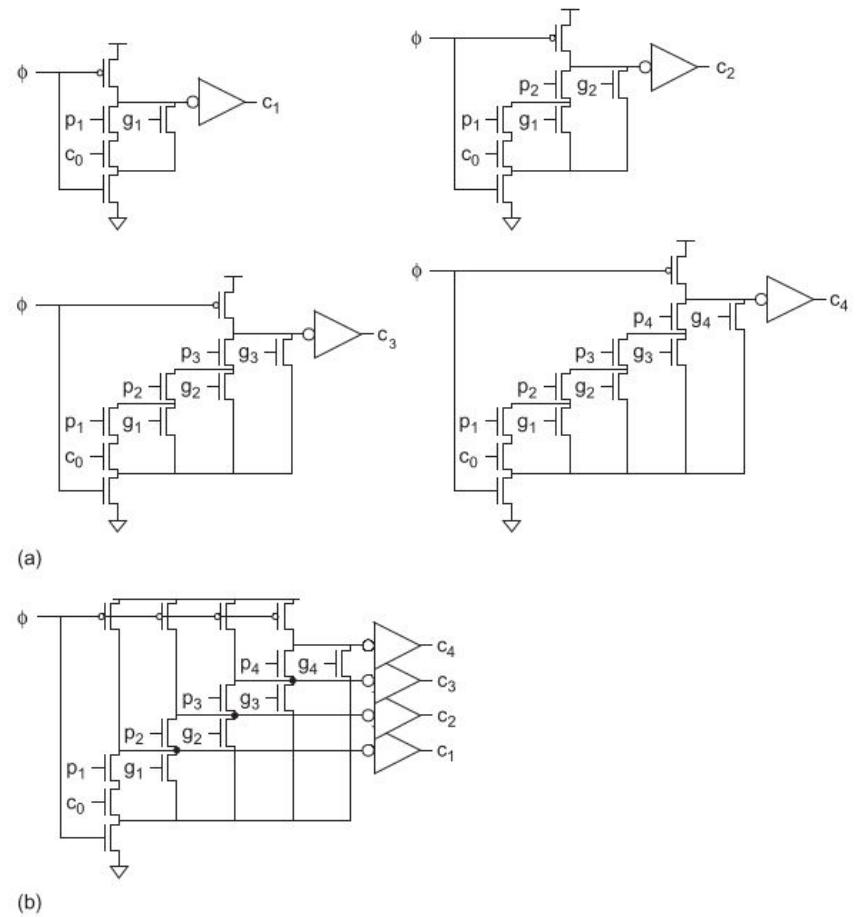
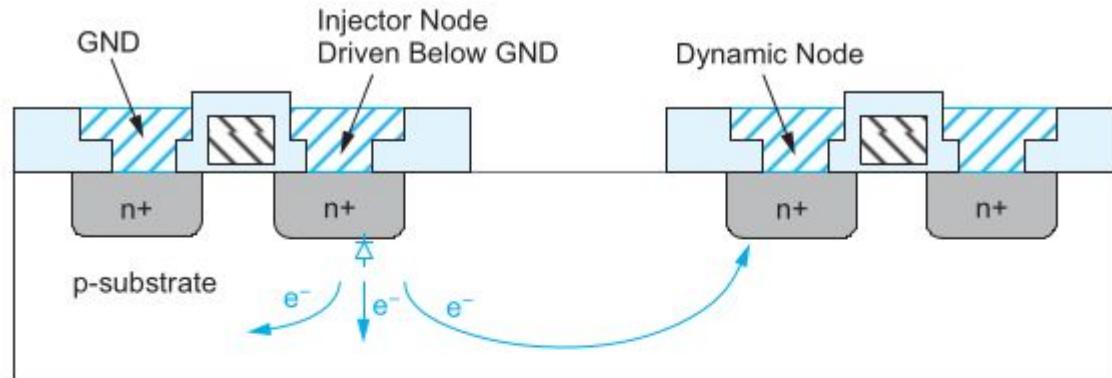


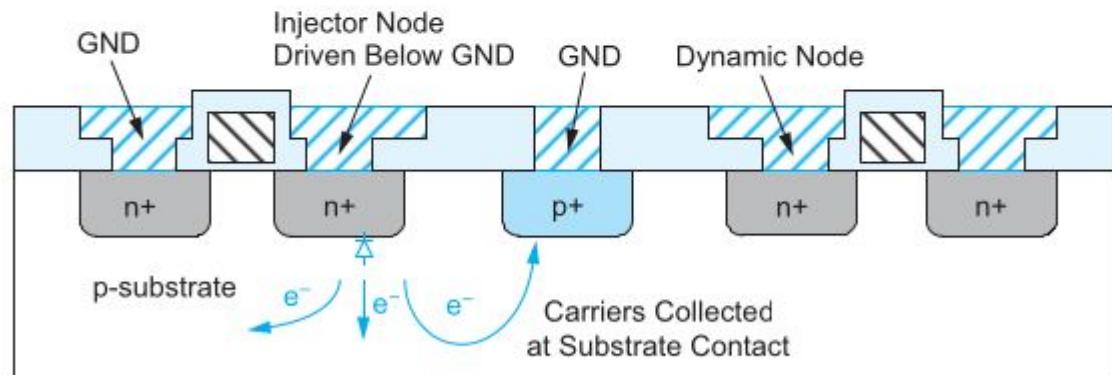
FIGURE 9.44 Conventional and MODL carry chains

Circuit Pitfalls

- ❖ Threshold drops
- ❖ Ratio failures
- ❖ Leakage
- ❖ Charge sharing
- ❖ Power supply noise
- ❖ Coupling
- ❖ Minority carrier injection
- ❖ Back-gate coupling
- ❖ Diffusion input noise sensitivity
- ❖ Race conditions
- ❖ Delay matching
- ❖ Metastability
- ❖ Hot spots
- ❖ Soft errors
- ❖ Process sensitivity



(a)



(b)

FIGURE 9.58 Minority carrier injection and collection

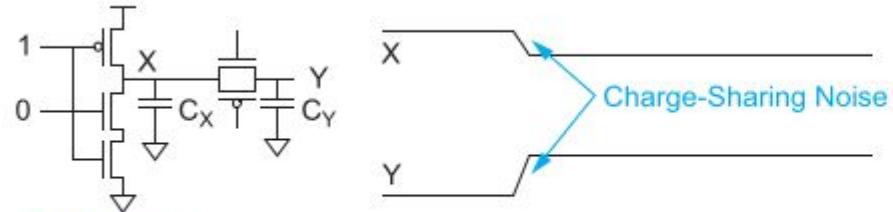


FIGURE 9.56 Charge sharing on dynamic gate driving pass transistor

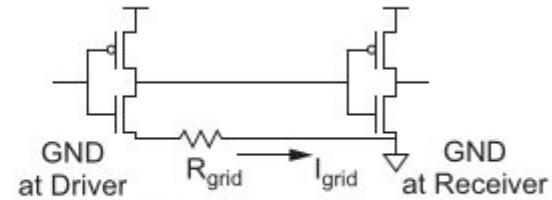


FIGURE 9.57 Power supply IR drops

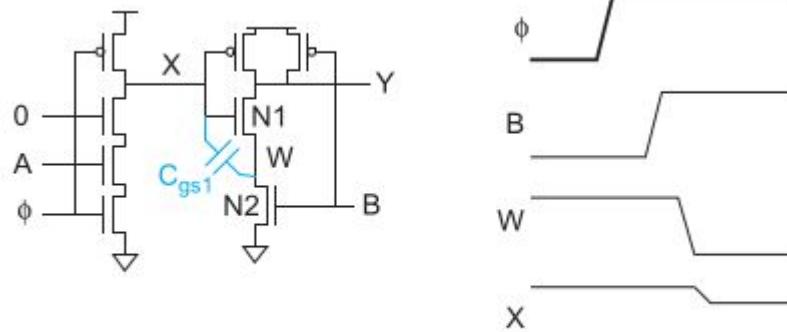


FIGURE 9.59 Back-gate coupling

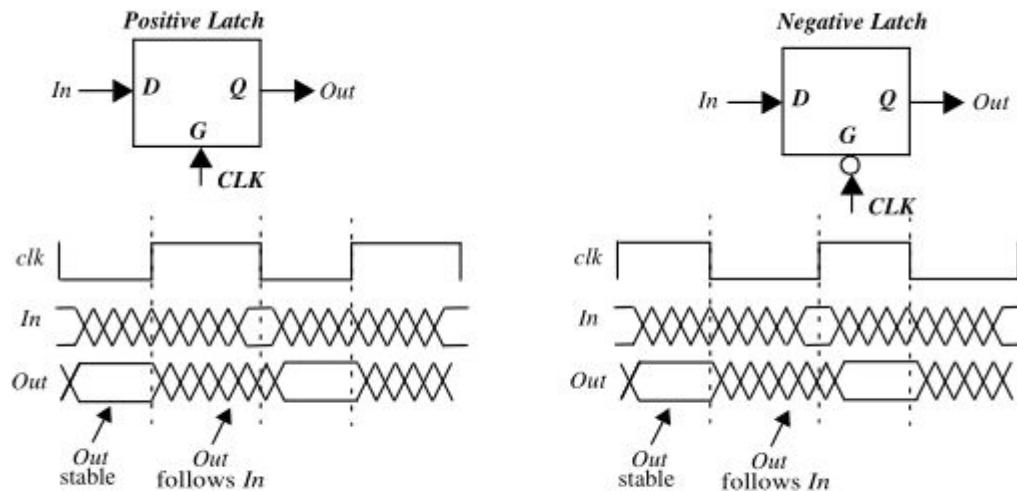


Figure 7.3 Timing of positive and negative latches.

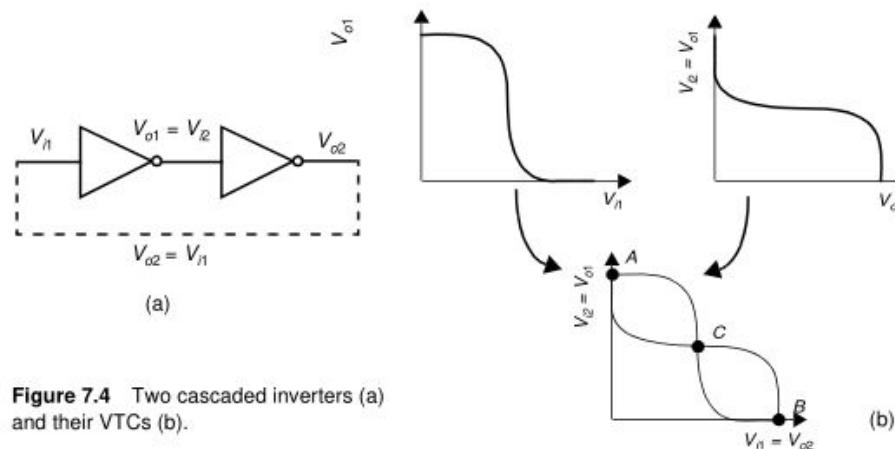


Figure 7.4 Two cascaded inverters (a) and their VTCs (b).

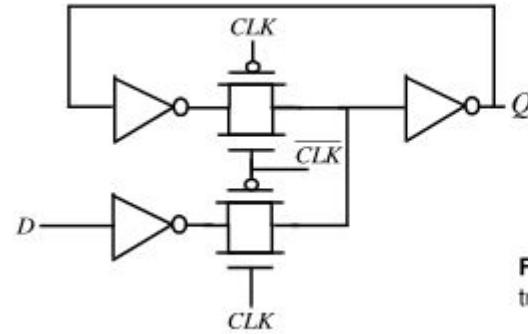
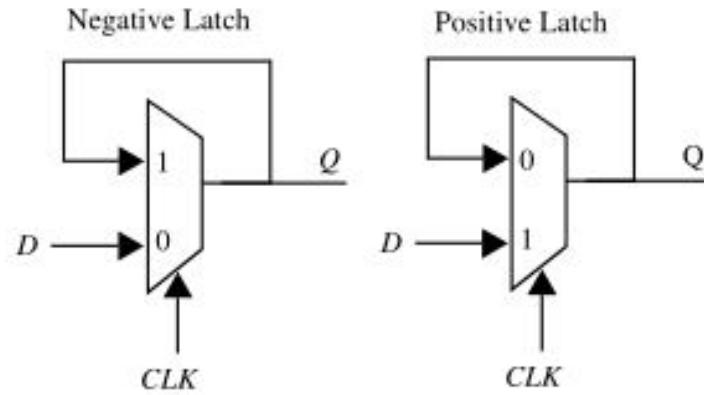
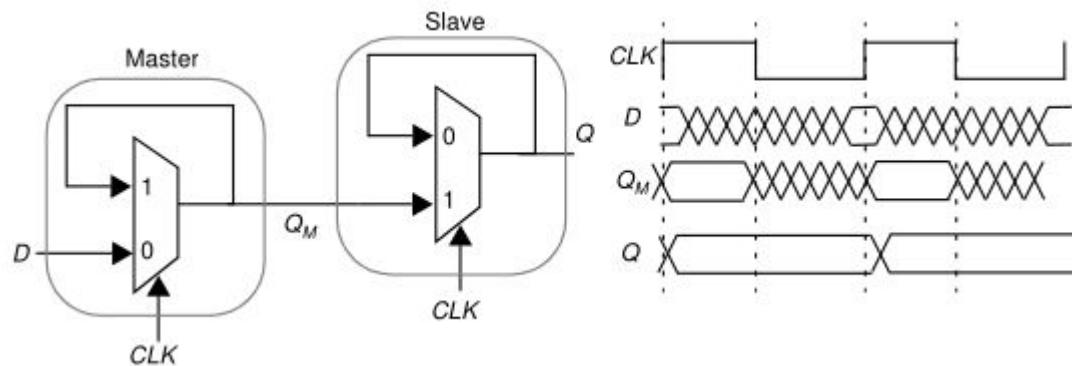


Figure 7.12 Positive latch built using transmission gates.



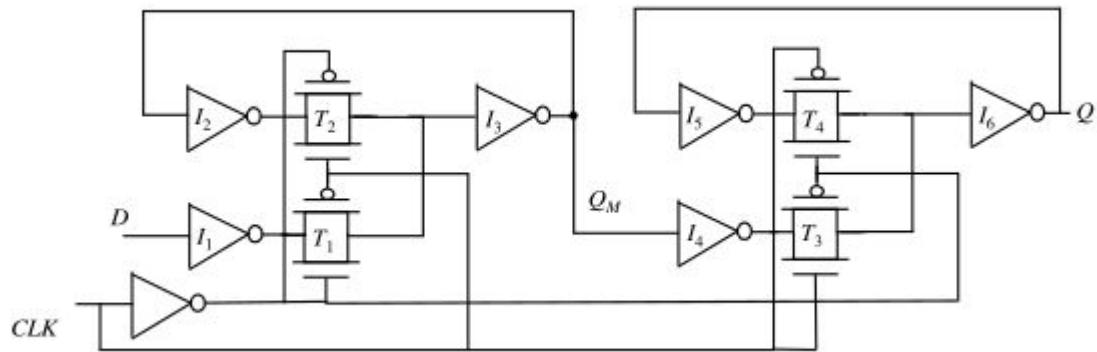


Figure 7.15 Master-slave positive edge-triggered register using multiplexers.

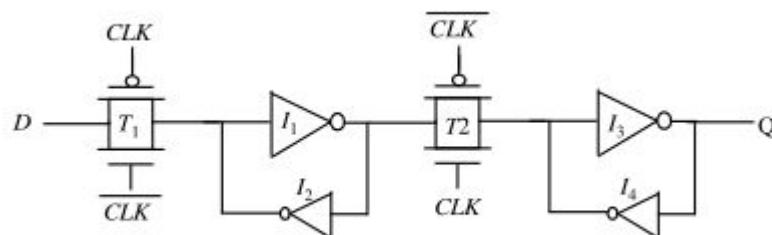


Figure 7.18 Reduced load clock load static master-slave register.

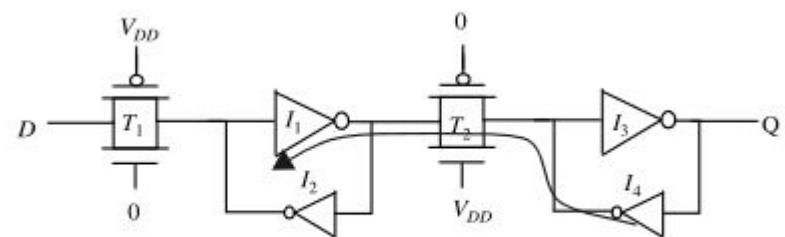
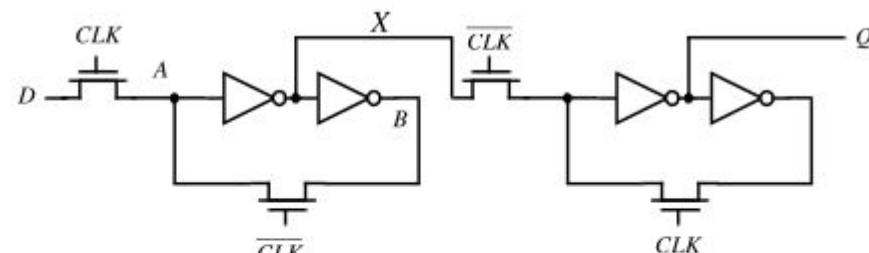


Figure 7.19 Reverse conduction possible in the transmission gate.



(a) Schematic diagram

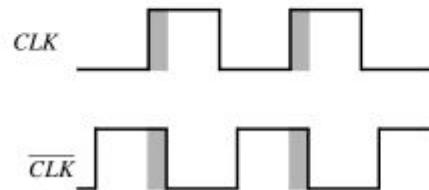
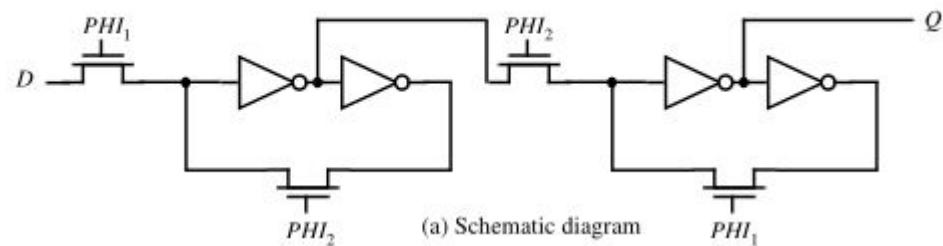
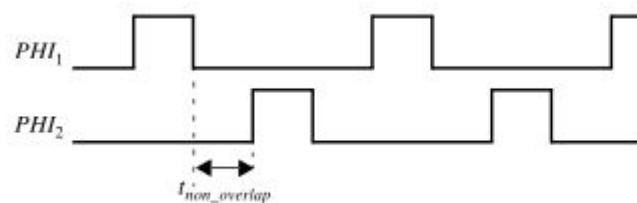


Figure 7.20 Master-slave register based on NMOS-only pass transistors.

(b) Overlapping clock pairs



(a) Schematic diagram



(b) Two-phase non-overlapping clocks

Figure 7.21 Pseudo-static two-phase D register.

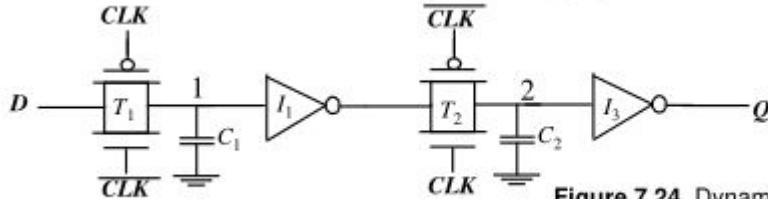


Figure 7.24 Dynamic edge-triggered register.

$$t_{overlap0-0} < t_{T1} + t_{I1} + t_{T2}$$

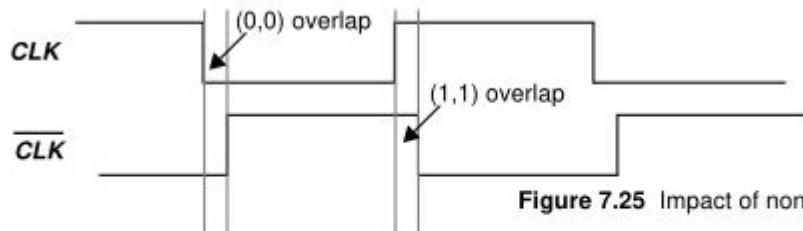
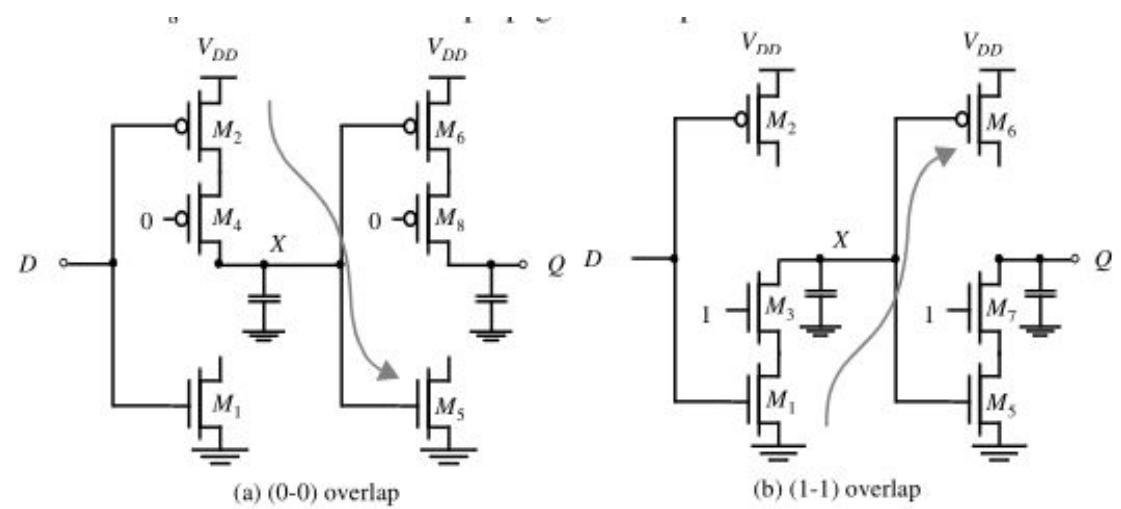
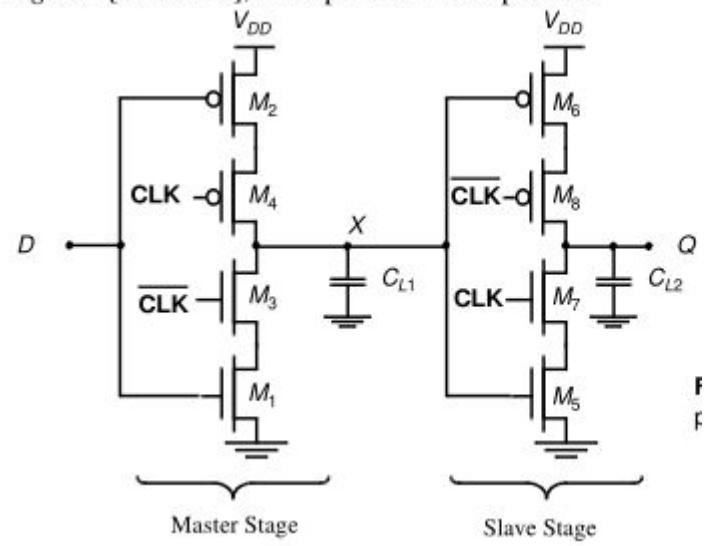


Figure 7.25 Impact of non-overlapping clocks.

Similarly, the constraint for the 1-1 overlap is given as:

$$t_{hold} > t_{overlap1-1}$$

Design, simulation, and operation in two phases



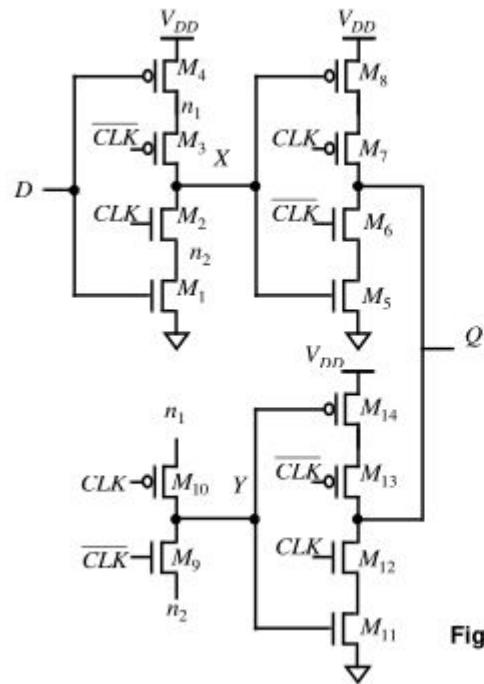


Figure 7.29 C²MOS based dual-edge triggered register.

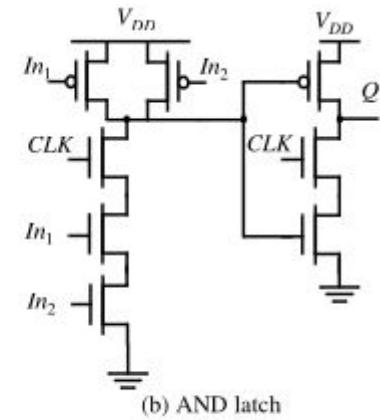
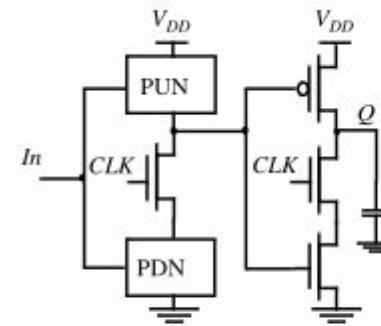
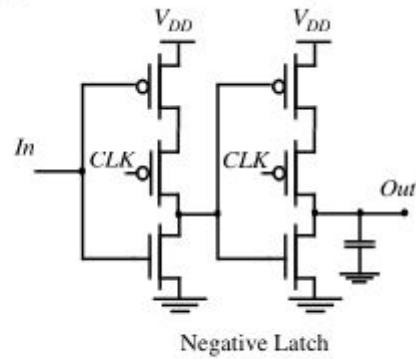
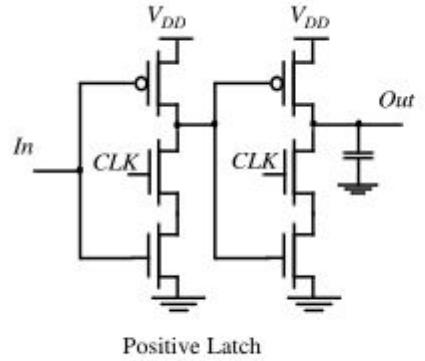


Figure 7.30 True Single Phase Latches.

(a) Including logic into the latch

Figure 7.31 Adding logic to the TSPC approach.

(b) AND latch

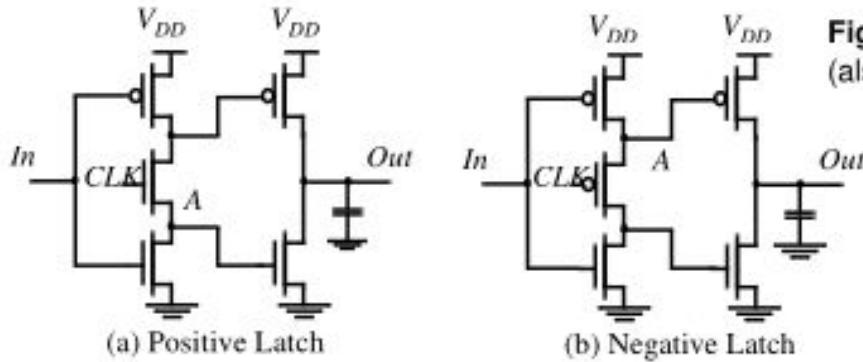


Figure 7.32 Simplified TSPC latch
(also called split-output).

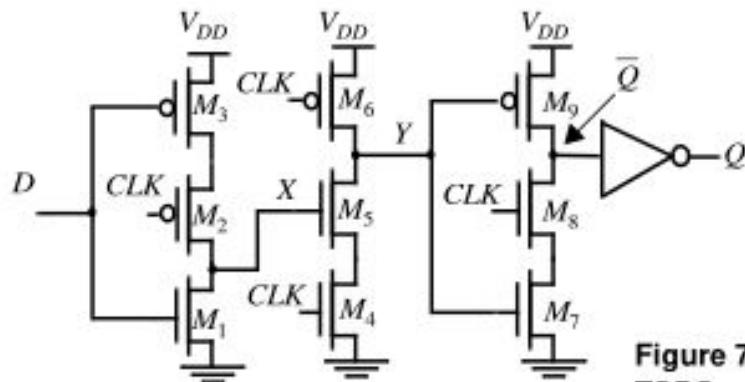


Figure 7.33 Positive edge-triggered register
TSPC.

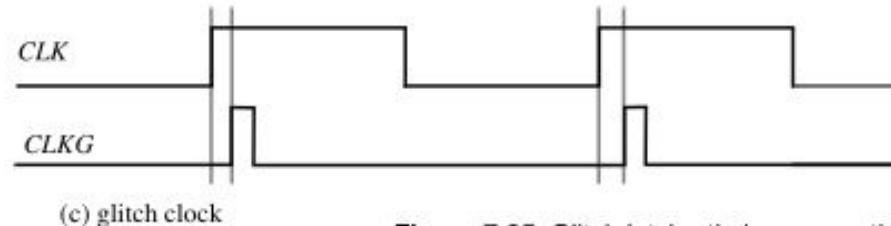
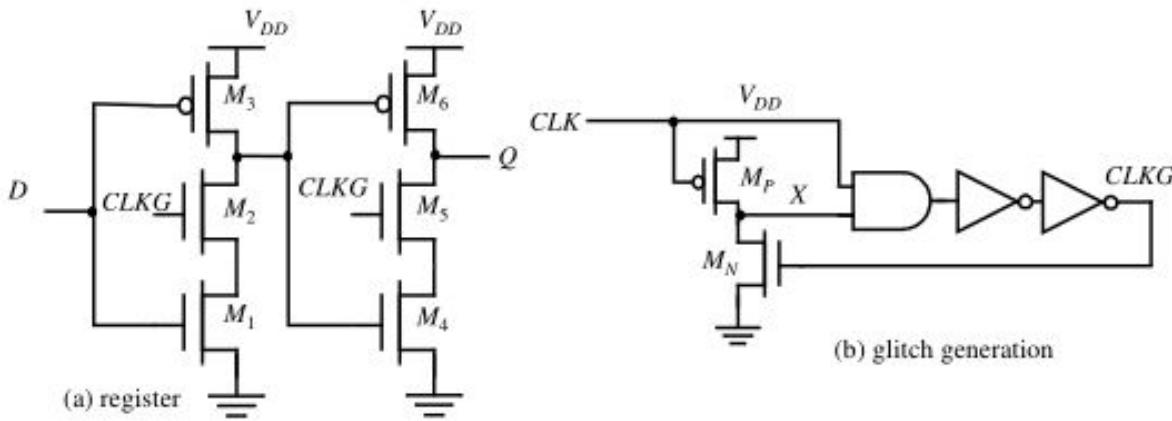


Figure 7.35 Glitch latch - timing generation and register.

